

2SD2158, 2SD2158A

Silicon NPN triple diffusion planar type

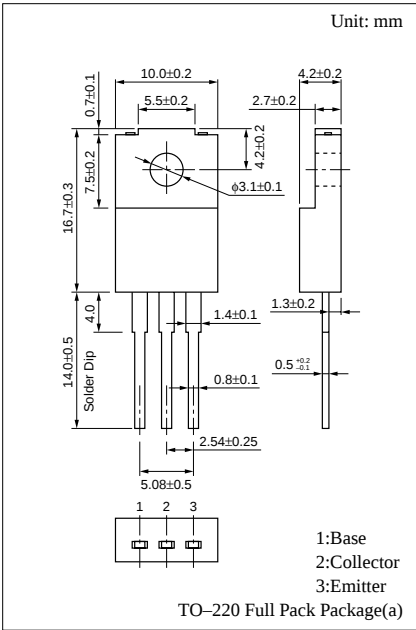
For power amplification with high forward current transfer ratio

■ Features

- High foward current transfer ratio h_{FE}
- Satisfactory linearity of foward current transfer ratio h_{FE}
- Full-pack package which can be installed to the heat sink with one screw

■ Absolute Maximum Ratings ($T_C=25^{\circ}C$)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	80	V
Collector to emitter voltage	V_{CEO}	60	V
Emitter to base voltage	V_{EBO}	6	V
Peak collector current	I_{CP}	4	A
Collector current	I_C	2	A
Base current	I_B	0.5	A
Collector power dissipation	P_C	20	W
Junction temperature	T_j	150	$^{\circ}C$
Storage temperature	T_{stg}	-55 to +150	$^{\circ}C$

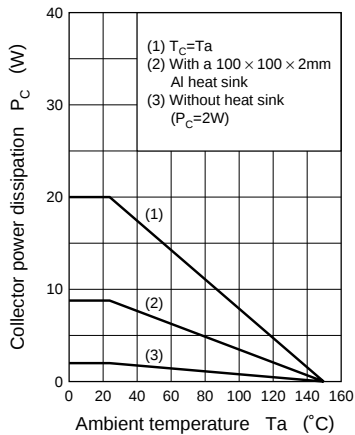
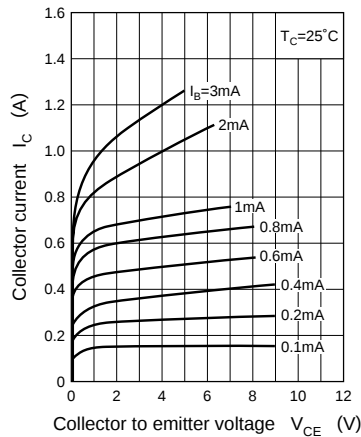
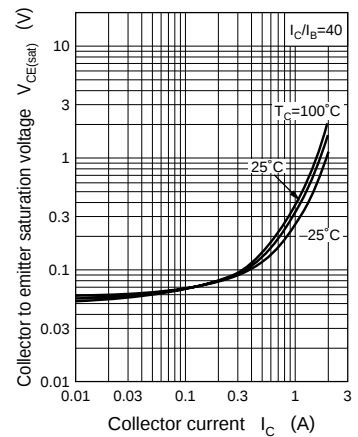
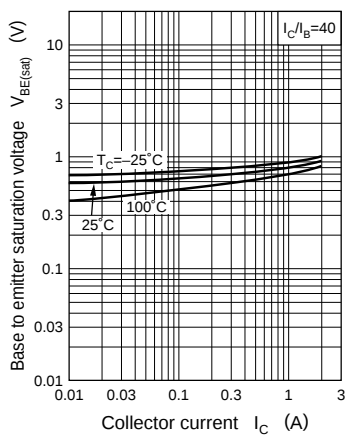
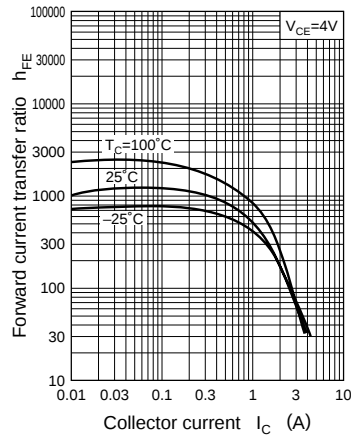
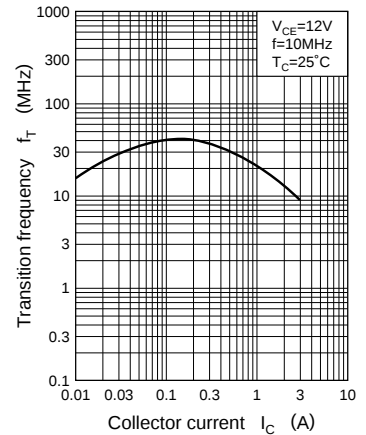
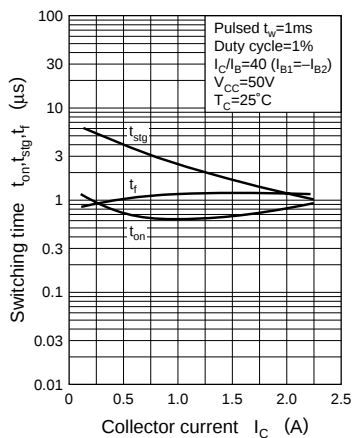


■ Electrical Characteristics ($T_C=25^{\circ}C$)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 80V, I_E = 0$			100	μA
Collector cutoff current	I_{CEO}	$V_{CE} = 40V, I_B = 0$			100	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 6V, I_C = 0$			100	μA
Collector to emitter voltage	V_{CEO}	$I_C = 25mA, I_B = 0$	60			V
Forward current transfer ratio	h_{FE}^*	$V_{CE} = 4V, I_C = 300mA$	500		2500	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 1A, I_B = 25mA$			1	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = 1A, I_B = 25mA$			1.2	V
Transition frequency	f_T	$V_{CE} = 12V, I_C = 200mA, f = 10MHz$		40		MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$		30		pF
Turn-on time	t_{on}	$I_C = 1A, I_{B1} = 25mA, I_{B2} = -25mA, V_{CC} = 50V$		0.6		μs
Storage time	t_{stg}			2.5		μs
Fall time	t_f			1		μs

* h_{FE} Rank classification

Rank	Q	P	O
h_{FE}	500 to 1000	800 to 1500	1200 to 2500

$P_C - T_a$  $I_C - V_{CE}$  $V_{CE(sat)} - I_C$  $V_{BE(sat)} - I_C$  $h_{FE} - I_C$  $f_T - I_C$  $t_{on}, t_{stg}, t_f - I_C$ 

Area of safe operation (ASO)

